## **Supplement Information**

## Effect of UV-Ozone Irradiation on Copper Doped Nickel acetate and Its Applicability to Perovskite Solar Cells

Jeongmo Kim, Hee Ryung Lee, Hyeong Pil Kim, Lin Tengda, Anil Kanwat, Abd. Rashid bin Mohd Yusoff and Jin Jang\*



Figure S1. Conductive atomic force microscopy(C-AFM) images  $(3\mu m \times 3\mu m)$  of Ni(ac) at V<sub>bias</sub> = 0.1 V. [Current profiles are obtained from horizontal lines at y axis of  $1\mu m$ ]



**Figure S2**. X-ray photoelectron spectroscopy (XPS) results of Cu:Ni(ac) and UVO-Cu:Ni(ac) thin films.; (a) survey scan. (b) O 1s narrow scan. (c) Ni 2p narrow scan. (d) Cu 2p narrow scan. [Reference peak is indicated inside.]



**Figure S3**. (a) Transmittances of thin films of PEDOT:PSS (31 nm), Ni(ac) (12 nm) and Cu:Ni(ac) (8 nm) respectively. (b) Optical transmittances of non-UVO irradiated 120 nm Cu:Ni(ac) films depending on copper doping ratio. (c) Optical transmittances of UVO-treated 120 nm Cu:Ni(ac) films.



**Figure S4**. Repeatability of  $R_s$ (Sheet Resistance) values for Cu:Ni(ac) thin films.; (a) without UVO treatment. (b) With UVO treatment.



Figure S5. Copper doping ratio dependent hall effect results.; (a) carrier concentration [/cm<sup>3</sup>]. (b) conductivity [S/cm]. (c) hall mobility  $[cm^2/V \cdot s]$ .



**Figure S6**. Schematic diagram of the MAPbI<sub>3</sub> crystallization process on the surface of thin films.; (a) on the PEDOT:PSS film (rms value = 1.482 nm). (b) on the UVO-Cu:Ni(ac) (rms value = 2.029 nm).



**Figure S7**. J-V characteristics of device performance measured at 100 mW/cm<sup>2</sup> based on Ni(ac) and UVO- Ni(ac) respectively.



**Figure S8**. Repeatability of device performances based on different hole transport layers of PEDOT:PSS, Ni(ac) and Cu:Ni(ac).; (a)  $J_{SC}(mA/cm^2)$ . (b)  $V_{OC}(V)$ . (c) FF(%) and (d) PCE(%).